



Faculty of Manufacturing Engineering

**DETERMINATION OF ELECTRICAL MEASUREMENT TO
DETECT POOR THERMAL DISSIPATION DEVICES USING
TRIZ**

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**DETERMINATION OF ELECTRICAL MEASUREMENT TO DETECT POOR
THERMAL DISSIPATION DEVICE USING TRIZ**

ONG MING CHUNG

**A thesis submitted
in fulfillment of the requirements for the degree of Master of Science
in Manufacturing Engineering**

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DECLARATION

I declare that this thesis entitled “Determination of Electrical Measurement to detect Poor Thermal Dissipation devices using TRIZ” is the result of my own research except as cited in the references. The thesis has not been accepted for any degree and is not concurrently submitted in candidature of any other degree.

Signature :

Name :

Date :

APPROVAL

I hereby declare that I have read this thesis and in my opinion this thesis is sufficient in terms of scope and quality for the award of Master of Science in Manufacturing Engineering.

Signature :

Supervisor Name :

Date :

DEDICATION

To my beloved parents, Ong Teck Lai and Phan Seow Lin.

Dedicated to my beloved wife, Deborah Chow Yen May.

Dedicated to my beloved brothers and sister in law.

Thank you for your support and encouragement.

ABSTRACT

Thermal dissipation of a microelectronic device is a topic of interest amongst the researchers because poor thermal dissipation may cause reliability problem during customer's application. Researchers found that Leadframe, Solder Paste Material, Chip Metalization and Die Attach process contributed to poor thermal dissipation of a device. The existence of air gap inside the package which was created during Die Attach process was found causing poor thermal dissipation for the device. Air gap blocks the heat dissipation path of the device, causing the heat to be entrapped inside the device which leads to poor reliability performance. X-Ray and Scanning Acoustic Microscopy (SAM) are widely used to identify air gap within microelectronic devices. However, these methods are only able to identify the poor thermal dissipation devices if it is related to the presence of air gap. Poor thermal dissipation can also caused by some weaknesses inherited from wafer processes. An alternative way to identify poor thermal dissipation devices is by using electrical measurement which has better advantages compared to X-Ray and SAM in terms of sampling size, time and effort. However, the challenge is on the effectiveness of the electrical measurement to identify poor thermal dissipation device because using low energy, the measurement may not be sensitive enough; but if using high energy, the device may become destructive. This is a typical contradiction found in this Inventive Problem which best solved by using "The Theory of Inventive Problem"-TRIZ because TRIZ deals with "Contradiction". Moreover, TRIZ stimulated new idea in solving the effectiveness problem in a structured approach. In this thesis, TRIZ proposed to use Parameter Change (PC) and Periodic Action (PA) as the solutions principle to increase the effectiveness of identifying poor thermal dissipation devices. Principle PC concluded that using V voltage, Y timing with 13.2Ampere as the input energy able to screen out device with poor thermal dissipation with 100% success rate; while Principle PA suggested that using input Energy of 900mJ able to achieve the same result. Experiment and data collection confirmed that TRIZ principle PC and PA are able to identify poor thermal dissipation in microelectronic device even though the device did not have air gaps. Such identification was not possible through traditional approaches, such as X-Ray or SAM.

ABSTRAK

Pelesapan haba peranti mikroelektronik adalah topik yang menarik di kalangan penyelidik kerana pelesapan haba yang lemah boleh menyebabkan masalah reliabiliti semasa aplikasi pelanggan. Para penyelidik mendapati bahawa Rangka Plumbum, Bahan Pateri Pes, Lapisan logam Cip dan Proses Pelekatan Cip menyumbang kepada pelesapan haba yang lemah. Kewujudan ruang udara di dalam pakej yang diwujudkan semasa Proses Pelekatan Cip didapati menyebabkan peranti mempunyai pelesapan haba yang lemah. Ruang udara ini menghalang jalan pelesapan haba peranti, menyebabkan haba akan terperangkap di dalam peranti ini sehingga peranti mengalami kerosakan dalaman. Secara umumnya, X-Ray dan Scanning Acoustic Microscopy (SAM) digunakan secara meluas untuk mengenal pasti jurang udara dalam peranti mikroelektronik. Walau bagaimanapun, kaedah ini hanya mampu untuk mengenal pasti peranti pelesapan haba yang lemah dalam peranti jika peranti mempunyai jurang udara. Pelesapan haba yang lemah pada peranti juga boleh diwarisi daripada proses wafer. Alternatif lain yang lebih baik untuk mengenal pasti pelesapan haba yang lemah dalam peranti adalah dengan menggunakan pengukuran elektrik yang mempunyai kelebihan yang lebih baik berbanding X-Ray dan SAM dari segi saiz persampelan, masa dan usaha. Akan tetapi, cabarannya adalah mengenai keberkesanan pengukuran elektrik untuk mengenal pasti pelesapan haba yang lemah dalam peranti kerana jika menggunakan tenaga yang rendah, ukurannya tidak cukup sensitif; namun jika menggunakan tenaga tinggi, peranti mungkin menjadi musnah. Ini adalah percanggahan yang biasa terdapat dalam Masalah Inventive ini yang dapat diselesaikan dengan menggunakan "The Theory of Inventive Problem" - TRIZ kerana TRIZ berurusan dengan "Percanggahan". Selain itu, TRIZ merangsang idea baru dalam menyelesaikan masalah keberkesanan dalam pendekatan yang berstruktur. Dalam tesis ini, TRIZ mencadangkan penggunaan Parameter Change (PC) dan Periodic Action (PA) sebagai prinsip penyelesaian untuk meningkatkan keberkesanan mengenal pasti peranti yang mempunyai lemah pelesapan haba. Prinsip PC menyimpulkan bahawa menggunakan V voltan, Y masa dengan 13.2Ampere sebagai input tenaga dapat mengenal pasti peranti yang mempunyai pelesapan haba yang lemah setinggi 100% keberkesanannya; manakala Prinsip PA mencadangkan dengan menggunakan input tenaga sebanyak 900mJ dapat mencapai keputusan yang sama. Eksperimen dan pengumpulan data mengesahkan bahawa prinsip TRIZ PC dan PA dapat mengenal pasti pelesapan haba yang lemah dalam peranti di mana ini tidak mungkin dicapai jika melalui pendekatan tradisional, seperti X-Ray atau SAM.

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TABLE OF CONTENTS

	PAGE
DECLARATION	
APPROVAL	
DEDICATION	
ABSTRACT	i
ABSTRAK	ii
ACKNOWLEDGEMENTS	iii
TABLE OF CONTENTS	iv
LIST OF TABLES	vii
LIST OF FIGURES	viii
LIST OF APPENDICES	xi
LIST OF ABBREVIATIONS	xii
LIST OF PUBLICATION	xiii
CHAPTER	
1. INTRODUCTION	1
1.1 Background	1
1.2 Problem Statement	3
1.3 Objectives	4
1.4 Scope of Study	5
1.5 Significance of Study	5
1.6 Thesis Outline	6
2. LITERATURE REVIEW	7
2.1 Introduction	7
2.2 Introduction to Microelectronics Manufacturing	8
2.3 Heat Dissipation Topic	12
2.4 Heat Dissipation Improvement	13
2.4.1 Heat Dissipation Improvement by Leadframe	15
2.4.1.1 Leadframe Materials	
2.4.1.2 Leadframe Design	
2.4.1.3 Leadframe Plating	
2.4.2 Heat Dissipation Improvement by Solder Paste Materials	17
2.4.3 Heat Dissipation Improvement by Chip Backside Metalization	18
2.4.4 Heat Dissipation Improvement by Die Attach Process	19
2.5 Weak Thermal Dissipation Device Detection	22
2.5.1 Weak Thermal Dissipation Device Detection by X- Ray	22
2.5.2 Weak Thermal Dissipation Device Detection by SAM	25
2.5.3 Weak Thermal Dissipation Device Detection by Infrared Thermography	27
2.5.4 Weak Thermal Dissipation Device Detection by Electrical Measurement	32
2.6 Problem Solving Tools	34
2.6.1 Design of Experiment(DOE)	34
2.6.2 TRIZ for Solving Inventive Problems	35
2.6.2.1 Example of TRIZ Application-Pizza Box Design	36

2.6.2.2	Example of TRIZ Application-Project Management	36
2.6.2.3	Example of TRIZ Application-Ecommerce Industry	38
2.6.2.4	Example of TRIZ Application-Chemical Process Safety	39
2.6.2.5	Example of TRIZ Application-Patent	40
2.6.2.6	TRIZ Application in Electrical Measurement	41
2.6	Summary	44
3.	METHODOLOGY	45
3.1	Introduction	45
3.2	TRIZ Approach	45
3.3	Sample Preparation Procedure	47
3.3.1	TRIZ Methodology	47
3.3.2	Sample Preparation	49
3.3.3	Data Collection and Analysis of Experimental Runs	51
4.	RESULTS AND DISCUSSIONS	
4.1	Introduction	57
4.2	TRIZ result and Analysis	57
4.2.1	Functional Model Development	57
4.2.2	Cause and Effect Analysis	58
4.2.3	Engineering Contradiction, System Parameters and Contradiction Matrix	59
4.2.4	TRIZ Solution Proposal	64
4.3	Experimental Results and Discussions	66
4.3.1	Validation on Principle “Parameter Change”	66
4.3.1.1	Negligible Air Gap Device versus Air Gap Device	66
4.3.1.2	Weak Thermal in Negligible Air Gap Device	69
4.3.1.3	Before and After “Parameter Change”	69
4.3.1.4	X-Ray, SAM and Electrical Measurement in identifying weak thermal dissipation	70
4.3.1.5	Validation on Principle “Parameter Change” with larger sample size	72
4.3.2	Validation on Principle “Periodic Action”	77
4.3.2.1	Single Pulse measurement	78
4.3.2.2	Multiple Pulses with same energy	80
4.3.2.3	Multiple Pulses with different Energy	83
4.3.2.4	Validation on Principle “Periodic Action” with Larger Sample Size	86
4.3.3	The Pros and Cons for “Parameter Change” and “Periodic Action”	95
4.4	Summary of Findings	96
5.	CONCLUSION AND FUTURE RECOMMENDATIONS	98
5.1	Introduction	98
5.2	Conclusion	98
5.2.1	To adapt Theory of Solving Inventive Problem (TRIZ) Approach in Exploring Alternatives for Weak Thermal Dissipation Device Detection by electrical measurement.	99

5.2.2	To prove that the cause of poor thermal dissipation device can be due to air gap within the device and device issue at silicon wafer level	100
5.2.3	To find the optimum energy level that can effectively identify poor thermal dissipation devices.	100
5.3	Future Recommendations	101
	REFERENCES	102
	APPENDICES	109

LIST OF TABLES

TABLE	TITLE	PAGE
2.1	Heat Dissipation Improvement supported by references	20
2.2	A Typical X-Ray Elements and its function	23
2.3	A Typical SAM Elements and its function	26
2.4	A Typical Infrared Thermography Elements and its function	29
2.5	Advantages of Electrical Measurement compared to X-Ray and SAM	32
2.6	References for Problem Solving Tools	43
3.1	Maximum Current Point for Measurement Timing X and Y from SOA Graph	53
3.2	Current Ramping for Measurement Timing X and Y	53
3.3	Periodic Action Validation Experiment	55
4.1	39 System Parameters	61
4.2	40 TRIZ Principles	62
4.3	Effectiveness of Electrical Measurement compared to X-Ray and SAM	70
4.4	Data Collection for Single Pulse	78
4.5	Measurement Delta between Device G1 and B1	80
4.6	Multiple Pulses for Energy AAAAA, BBBBB and CCCCC	81
4.7	Measurement Delta between Device G2 and B2	82
4.8	The Pros and Cons for Principle “Parameter Change”	96
4.9	The Pros and Cons for Principle “Periodic Action”	96

LIST OF FIGURES

FIGURE	TITLE	PAGE
2.1	Simplified Wafer Manufacturing Processes	9
2.2	Simplified Assembly Processes	11
2.3	A typical Microelectronics Device	13
2.4	An illustration on how the heat is being transferred from the package to outer environment	14
2.5	An illustration on how the heat is being transferred from the package to outer environment with the air gap inside Solder Paste Material.	14
2.6	A typical X-Ray System	23
2.7	A typical simplified SAM System	26
2.8	A simplified Infrared Thermography system	28
3.1	TRIZ Approach Modeling	46
3.2	Overall Methodology Flowchart	48
3.3	Sample Preparation for Simulated and Negligible Air Gap Device	49
3.4	Sample Preparation for Good and Weak thermal dissipation device from negligible air gap device	50
3.5	An Example of Safe Operating Area Graph	52
3.6	Template on Graph “ Before Parameter Change” and Graph “After Parameter Change”	54
3.7a	Template for Graph Single Pulse measurement	55
3.7b	Template for Graph Multiple Pulses with same energy	56
3.7c	Template for Graph Multiple Pulses with different energy	56
4.1	Electrical Measurement Functional Model	58

4.2	Cause and Effect Analysis for ineffective identification of weak thermal dissipation device.	59
4.3	Engineering Contradiction, System Parameter, Contradiction Matrix	60
4.4	Online Contradiction Matrix	64
4.7a	SAM Images from Group A samples with negligible air gap	67
4.7b	SAM Images from Group B samples with air gap	67
4.8	Graph before “Parameter Change” for Good and weak thermal dissipation device	68
4.9	Graph After “Parameter Change” for Good and weak thermal dissipation device	68
4.10	Example of SAM images with air gap and negligible air gap for Experiment Parameter Change with larger sample size	73
4.11	Graph Before “Parameter Change” with larger sample size	74
4.12	Graph After “Parameter Change” with larger sample size	75
4.13	Normality test for Parameter Before and After Change using CEDA	76
4.14	Indistinguishable SAM images for good and bad thermal dissipation device from group with negligible air gap.	77
4.15	The output response for G1 and B1 using Single Pulse with Energy A, B and C.	79
4.16	The average reading for G1 and B1 using different Energy A, B and C	80
4.17	The output response for G2 and B2 using Multiple Pulses with Energy AAAAA, BBBBB and CCCCC.	82
4.18	The average reading for G2 and B2 using Energy AAAAA, BBBBB and CCCCC.	83
4.19	The output response for G3 and B3 using Multiple Pulses with Energy AABBB, BBCCC and CCDDD.	85
4.20	Example of 4 SAM Images taken from 26 devices for Periodic Action Experiment.	86
4.21	The output response for 26 devices using Single Pulse Energy	88
4.22	The output response for 26 devices using Multiple Pulses with Energy AAAAA, BBBBB and CCCCC.	89
4.23	Normality Test for Energy AAAAA, BBBBB and CCCCC	91
4.24	ANOVA test for Energy AAAAA, BBBBB and CCCCC	91

4.25	The output response for 26 devices using Multiple Pulses with Energy AABBB, BBCCC and CCDDD.	93
4.26	Normality Test for Energy A, B, C and D	94

LIST OF APPENDICES

APPENDIX	TITLE	PAGE
A	SAM images for “Parameter Change” Experiment with larger sample size	109
B	Multiple Pulses with Energy AABBB, BBCCC and CCDDD	111
C	SAM images for “Periodic Action” Experiment with larger sample size	112
D	Single Pulse with Larger Sample size	113
E	Multiple Pulses with Energy AAAAA, BBBBB, and CCCCC (larger sample size)	115
F	Multiple Pulse with Energy AABBB, BBCCC and CCDDD (larger sample size)	117

LIST OF ABBREVIATIONS

Ag	– Silver
Ag–Al	– Silver–Aluminium
Al	– Aluminium
ANOVA	– Analysis of Variance
Au	– Gold
Au–Sn	– Gold–Tin
BSM	– Backside Metallization
Cu	– Copper
DC	– Direct Current
DI	– Deionised
DOE	–Design of Experiment
MOSFET	– Metal Oxide Semiconductor Field Effect Transistor
Pb–Sn	– Lead–Tin
PC	– Process Control
PCT	– Power Cycling Test
RSM	– Response Surface Modelling
SAM	– Scanning Acoustic Microscopy
SEM	– Scanning Electron Microscopy
SiC	– Silicon Carbide
SOA	– Safe Operating Area
TRIZ	– Theory of Solving Inventive Problem

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CHAPTER 1

INTRODUCTION

1.1 Background

Microelectronics devices are being used in various applications, from consumer application such as smartphone to automotive application such as air bag module for safety aspect. Due to the various applications, microelectronics packaging is essential to protect the fragile silicon chips when they are operating under the extreme hot and cold environment. One of the packaging technologies that are widely used in Microelectronics manufacturing is the plastic packaging technology. In plastic packaging technology the silicon chip is attached to the lead-frame during die attach process and encapsulated by thermoset plastic material by means of transfer molding process. The function of the plastic package is not only to protect the silicon chip; it also provides a medium to dissipate heat generated by the silicon chip to the outer environment.

One of the inherent issues in plastic packaging technology is the presence of entrapped air inside the plastic package which causing the degradation of thermal dissipation capability of the Microelectronics device. The presence of air gap within the package forces the heat to be dissipated through another cooler and longer thermal dissipation path. Such longer thermal dissipation path would cause the package to have lower thermal impedance as suggested by Katsis and Daniel (2006). Therefore, the heat entrapped within the package would cause a temperature rise in the package and would result in higher junction temperature and weaker reliability performance. Subsequently, the device may become malfunction and risk end user's life especially when the device failed

to operate in its normal operating mode. Such weak thermal dissipation devices need to be identified and isolated before reaching customer.

There are various research works done in minimizing the impact for weak thermal dissipation devices. Some of the researches being done are in the area of materials development such as lead-frame materials as discussed by Li et al. (2012); Yang et al. (1999) and Ohtaka et al. (1996). Improvement on lead-frame design to improve the thermal dissipation were shared by Lee and Chien (1997); Wu et al. (2012); Pardo et al. (2013) and Xian and Choon (2013). Aside lead-frame materials and lead-frame design, research works in solder paste materials were done by Li et al. (2010), Yussef et al. (2015), Siow (2012), Manikam et al. (2012) and Kim and Nishikawa (2014) in which solder paste material plays an important role to improve the thermal dissipation of a microelectronics device. Goran et al. (1990), Thang et al. (2005) and Olsen and Berg (1979) researched in chip metallization concluded the use of Au-Sn as chip backside metallization can achieve air gap free die attach process which contribute to the good thermal dissipation. Aside from materials development, process optimization works were also explored by Yu et al. (2008) and Thang et al. (2005) during die attach process while Yen et al. (2014) and Lee et al. (2008) research on molding process which utilize simulation tool to analysis and optimize molding design in reducing the air gap formation during molding process.

1.2 Problem Statement

Despite those research efforts to improve thermal dissipation, air gap formation still presents as one of the major issue in microelectronics packaging. Therefore, the ability to screen those weak thermal dissipation devices is important. Currently, most of the Microelectronics manufacturing operations still performing X-Ray or SAM (Scanning Acoustic Microscopy) in sampling basis to screen out potential weak thermal dissipation devices due to the present of air gap. These screening processes are cumbersome, complicated process, needs additional efforts and time consuming, often limited by sampling basis. Thermography or Infrared may be good in screening out weak thermal dissipation device, but different material has different emissivity, therefore, the interpretation of the captured data in images form becomes harder and complex. The image processing may still subject to certain inaccuracy due to some noise, and require additional process to segment and filter before producing the final desired outcome. Also, Thermography is not suitable to be used as one of the screening process in production due to the low Unit per hour (UPH) and its image processing inaccuracy. On the contrary, electrical measurement can fit in the gap because using electrical measurement as a screening method is less complicated yet effective and can have 100% screening compared to X-Ray, SAM and Infrared. Moreover, if the device inherits weaknesses from wafer process, the device may not have air gap, but still can have weak thermal dissipation as mentioned by Wolfgang (2007) and Schulze et al. (2013). Such weak thermal dissipation devices are not able to be screened out by traditional screening methods such as X-Ray or SAM but only by electrical measurement.

Electrical measurement provides more advantages over the X-Ray and SAM methods with 100% sampling to identify the weak thermal dissipation devices. However, the challenge is to determine the optimum level of energy to be used during electrical

measurement process, if the measurement energy is too low, the measurement may not be sensitive enough; but if the measurement energy is too high, the device may become defective. Such typical contradiction found in Inventive Problem which is best solved by using “The Theory of Inventive Problem”-TRIZ because TRIZ deals with “contradiction”. Moreover, TRIZ is a structured inventive problem solving methodology and TRIZ can also stimulate new idea in solving the effectiveness problem. Due to limited research works or journals being published on the application of TRIZ in electrical measurement, this could be one of the challenges in this study. Nevertheless, in this study, the application of TRIZ in solving electrical effectiveness problem to identify the weak thermal dissipation device was demonstrated.

1.3 Objectives

Specific objectives to be achieved in this study are:

- To adopt Theory of Solving Inventive Problem (TRIZ) approach in exploring alternatives for weak thermal dissipation devices detection by electrical measurement.
- To prove that the cause of poor thermal dissipation device can be due to air gap within the device and device issue at silicon wafer level.
- To find the optimum energy level that can effectively identify poor thermal dissipation devices.

1.4 Scope of Study

This research adopted TRIZ approach which is a structured inventive problem solving methodology in electrical measurement to explore new idea in solving the effectiveness in identifying weak thermal dissipation devices on Metal Oxide Semiconductor Field Effect Transistor (MOSFET) device. Experiments were done in modifying the input energy of the parameter setting to validate the two TRIZ principles, “Parameter Change” and “Periodic Action”. The device used in this study has chip thickness between 100µm to 130µm and the chip size between 20 mm² to 25 mm². Copper (Cu) leadframe material was used in this device. This MOSFET device was with eight pins where the pins connected to Gate, Drain and Source terminal for its switching functionality. The experiments were conducted in a controlled room temperature of 25°C with tolerance of plus and minus 2 to 3°C.

1.5 Significance of Study

- This study was reference to TRIZ systematic approach to solve the Inventive Problem. The steps which led to an alternative solution were provided in this thesis which served as a reference for other TRIZ application in any other field.
- This study was also to prove and correct the wrong concept of “Weak device is solely depends on air gap alone”. In other words, many perceived that if there is no air gap exists within the package, the device should be considered as good device. Hence, proven by experiment data, this wrong concept was able to be corrected.
- With the effectiveness of this electrical measurement in identifying weak thermal dissipation devices, X-Ray or SAM process could be removed as one of the manufacturing process and in Failure Analysis process cycle.

1.6 Thesis Outline

This thesis was divided into five chapters. In Chapter 1, an introduction of this research was presented. Background, problem statement, objectives, scope of study, significance of study and the outline were discussed.

In Chapter 2, literature review on what cause weak thermal dissipation device and the improvement activities on heat dissipation were discussed, focusing on leadframe, solder paste, wafer metallization and die attach processes. Besides, the ways in identifying the solder air gap in assembly and their limitations were discussed in which electrical measurement was proven to have more advantages than the other options.

In Chapter 3, flow chart of the experiment was shown and explained. With this, a clearer picture on the whole experiment setup was clearly defined with some figures provided. Firstly, TRIZ approach was used and introduced. Secondly, Sample preparation process was discussed. Thirdly, the experiments to validate the TRIZ principles were discussed.

In Chapter 4, all data from sub experiments were compiled systematically. Basically, it was divided into two portions where the first portion was on validating the TRIZ principle “Parameter Change” while the second portion was about validation on TRIZ principle “Periodic Action”. Several observations were made after analyzing the data.

Lastly, in Chapter 5, a summary of this study was presented as well as recommendation was provided for future study.